

REMARKS

Applicant appreciates the thorough examination of the present application as evidenced by the Final Office Action of June 26, 2006. Applicant has amended independent Claim 9 to include the recitations of dependent Claim 11, to further clarify the differences between the claims of the present invention and the cited reference. Applicant has cancelled Claim 11 from the present application. Applicant has also amended dependent Claims 12-16 and 28 to conform the dependencies thereof to the cancellation of Claim 11. Applicant respectfully requests that the present amendment be entered as it merely incorporates the recitations of a dependent claim into an independent claim, thus, the combination has already been examined. Applicant respectfully submits that amended independent Claim 9 and the claims that depend therefrom are in condition for allowance for at least the reasons discussed herein.

The Section 102 Rejections

Claims 9-16 stand rejected under 35 U.S.C. § 102(b) as being anticipated by United States Patent No. 6,100,118 to Shih *et al.* (hereinafter "Shih"). *See* Office Action, page 2. Applicant respectfully disagrees. For example, amended Claim 9 recites:

A method of forming an integrated circuit device, comprising:
forming a window layer on an integrated circuit substrate that defines a fuse region such that the window layer is formed at an upper portion of the integrated circuit device and recessed beneath a surface of the integrated circuit device;
forming a conductive layer pattern and a buffer pattern on the integrated circuit substrate between the integrated circuit substrate and the window layer, the buffer pattern being between portions of the conductive layer pattern on the integrated circuit substrate; and
forming a fuse pattern between the buffer pattern and the window layer;
wherein forming the buffer pattern comprises:
forming a first buffer pattern;
forming a first insulation layer between the first buffer pattern and the fuse pattern, the fuse being formed on the first insulation layer;
forming a second buffer pattern between the first buffer pattern and the integrated circuit substrate; and
forming a second insulation layer between the second buffer pattern and the first buffer pattern, the conductive layer pattern and the first buffer pattern being formed on the second insulation layer.

Applicant respectfully submits that at least the highlighted recitation of amended Claim 9 is neither disclosed nor suggested by Shih for at least the reasons discussed herein.

As a preliminary note, since the rejections in the Final Office Action are identical to the rejections set out in the previous action, Applicant hereby incorporates the arguments set out in Applicant's previous response of September 22, 2005 as if set forth in their entirety herein. Applicant will not repeat those arguments in the interest of brevity.

Before addressing the 102 rejection, Applicant will respond to statements made in the Response to Arguments section of the Office Action. Responsive to Applicant's argument that the previous Office Action never points to which elements of Shih which portion of Shih supposedly discloses the buffer pattern as recited in Claim 9, the Final Office Action states that "the features upon which applicant relies (i.e., the buffering function during the repairing process, which may reduce an impact applied to the substrate by a laser beam) are not recited in the rejected claim(s)." *See* Final Office Action, page 5. Applicant respectfully submits that the Final Office Action misinterprets Applicant's argument. Applicant merely cited the specification of the present invention to illustrate a function of the buffer pattern recited in Claim 9. However, the feature upon which Applicant relies, *i.e.*, the buffer pattern, is clearly recited in Claim 9. The Final Office Action goes on to spell out various case holdings responsive to Applicant's argument (*See* Final Office Action, pages 4-7), but still fails to point out which element in Shih discloses or suggests the buffer pattern as recited in Claim 9. Accordingly, Applicant once again respectfully requests that if the rejection of Claim 9 is maintained, that the elements which supposedly teach the recitations of Claim 9 be pointed out. In particular, Applicant requests that that the element which supposedly teaches a buffer pattern as recited in Claim 9 be pointed out.

As discussed above, Claim 9 has been amended to include the recitations of dependent Claim 11 and Claim 11 has been cancelled from the present application. In particular, amended Claim 9 recites forming first and second buffer patterns as set out above. As further recited in amended Claim 9, a first insulation layer is formed between the first buffer pattern and the fuse pattern and the second buffer pattern is formed between the first buffer pattern and the integrated circuit substrate. In other words, the first buffer pattern is positioned below the fuse pattern and the second buffer pattern is positioned under the first buffer pattern. As discussed in detail in Applicant's previous response, although Shih does discuss a metal fuse and a plurality of metal fuse lines, nothing in Shih discloses or suggests first and second buffer patterns formed under the fuse pattern as recited in amended Claim 9. Accordingly, Applicant respectfully submits that amended Claim 9 is patentable over Shih

for at least the reasons discussed herein. Furthermore, the dependent claims are patentable at least per the patentability of independent Claim 9 from which they depend.

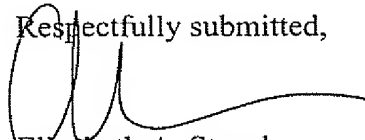
Many of the dependent claims are also separately patentable. For example, Claim 13 also recites forming a second buffer pattern and details associated with forming the first and second buffer patterns. As discussed above, nothing in Shih discloses or suggests one or more buffer patterns.

Claim 14 recites "forming a line pattern between the integrated circuit substrate and the second insulation layer adjacent the second buffer pattern." Again, as discussed above, nothing in Shih discusses a buffer pattern. Therefore, it follows that nothing in Shih discloses or suggests forming a line pattern adjacent the second buffer pattern as recited in Claim 14. Accordingly, Claim 14 is separately patentable over Shih for at least these additional reasons.

CONCLUSION

Applicant respectfully submits that the pending claims are patentable over the cited references for at least the reasons discussed herein. Accordingly, Applicant respectfully submits that the pending claims are in condition for allowance, which is respectfully requested in due course.

Respectfully submitted,




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